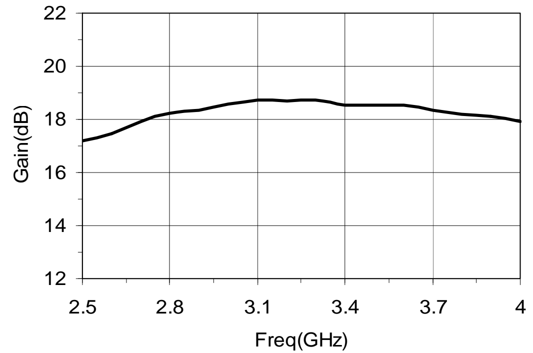
Features

- Frequency：2.5GHz～4.0 GHz
- Gain：18 dB
- Psat：45dBm
- P.A.E.：40%
- +24V@2.1A(Quiescent)
- Chip Size：3.65mm×5.10mm×0.10mm



Electrical Specification (TA=+25℃, Vg=-1.7V, Vd=+24V)

Parameter	Min.	Typ.	Max.	Unit
Frequency	2.5～4.0			GHz
Psat		45		dBm
Power Gain		18		dB
Gain Flatness			±0.6	dB
P.A.E.		40		%
VSWRin			2.5	-
Operating Current			3.5	A

Note：1）All chips have been on-chip 100% DC and RF tested.

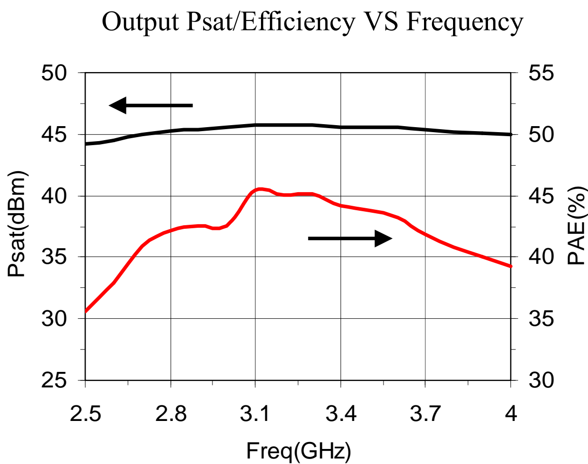
（2）Test Condition：Vd =+24V；Vg =-1.7V，Pin=27dBm.

Limited Rating Values

Vds	+32V
Vgs	-5V
Input CW Power	+25dBm
Channel Temperature	+175℃
Storage Temperature	-65℃～+150℃

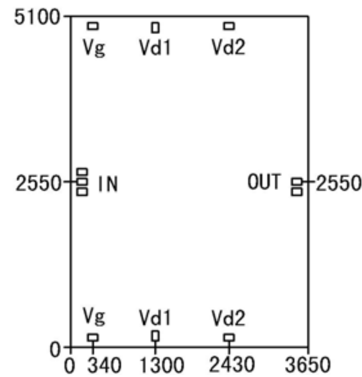
Typical Testing Curves

Output Psat/Efficiency VS Frequency



Dimensions and Outline

NC11623C-2540P30 outline



Note：The unit is um .

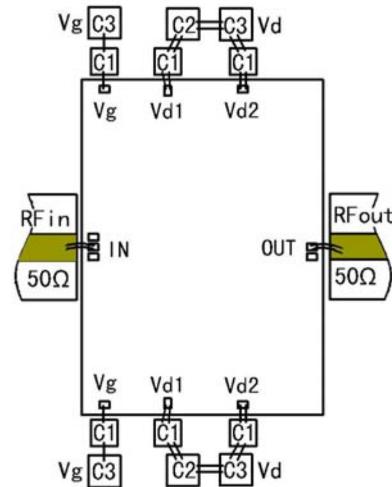
Dimension of input/output pad:150×100μm^2.

Dimension of bonding pad Vg: 150×100μm^2.

Dimension of bonding pad Vd1:100×150μm^2.

Dimension of bonding pad Vd2:150×100μm^2.

Assembly Diagram



Note： External capacitor C1=100pF， C2=1000pF， C3=10000pF.

Attention

1） Bonding with 80/20 Au/Sn. The temperature should be lower than 300℃ and the time should be less than 30 seconds.
2） Gold wires (diameter: 25μm～30μm) are suggested to be used. The temperature of bonding platform should not exceed 250℃.
3） Blocking capacitors in Input/Output are already integrated.
4） Antistatic protection should be taken.